

Numerical Study of the Localization-Delocalization Transition for Vibrations in Amorphous Silicon

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Numerical studies of amorphous silicon in harmonic approximation show that the highest 3.5% of vibrational normal modes are localized. As vibrational frequency increases through the boundary separating localized from delocalized modes, near $\omega_c=70\text{meV}$, (the “mobility edge”) there is a localization-delocalization (LD) transition, similar to a second-order thermodynamic phase transition. By a numerical study on a system with 4096 atoms, we are able to see exponential decay lengths of exact vibrational eigenstates, and test whether or not these diverge at ω_c . Results are consistent with a localization length ξ which diverges above ω_c as $(\omega - \omega_c)^{-p}$ where the exponent is $p \sim 1.3 \pm 0.5$. Below the mobility edge we find no evidence for a diverging correlation length. Such an asymmetry would contradict scaling ideas, and we suppose it is a finite-size artifact. If the scaling regime is narrower than our ($\approx 1\text{ meV}$) resolution, then it cannot be seen directly on our finite system.

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Harmonic normal modes of vibration can be classified as extended or localized. In dimension $d = 3$, the vibrational spectrum has sharp boundaries (“mobility edges”) separating these two kinds of modes. The sudden change at the mobility edge is a “localized to delocalized” (LD) transition (Anderson, 1958). Anderson’s paper considered localization of electronic wavefunctions, and most subsequent work focussed on this case (Lee and Ramakrishnan, 1985; Kramer and MacKinnon, 1993; Belitz and Kirkpatrick, 1994; Ohtsuki, Slevin, and Kawarabayashi, 1999). Harmonic vibrations (treated classically – quantization does not matter for localization) have similar wave properties to electrons in independent-electron approximation. However, in one respect, vibrational states differ from electron states. Long wavelength, low frequency (sound) modes always exist, extending throughout a homogeneous sample, and are thus delocalized. There is no analog of this “gapless” mode for electrons. Nevertheless, it is generally believed that at higher frequencies, vibrations and electrons have similar localization properties (Kirkpatrick, 1985; Sheng, Zhou, and Zhang, 1994; Sheng, 1995; Akita and Ohtsuki, 1998).

In glasses, only a few percent of normal modes can propagate ballistically like sound. As frequency increases, ballistic character is lost at typical frequencies of 10 meV (Rat *et al.* 1999), but the LD transition (which is hard to probe by direct experiment) is postponed to a much higher frequency ω_c (Allen and Feldman 1989; Feldman *et al.* 1991; Sheng, Zhou, and Zhang 1994; Finkemeier and von Niessen 1998; Pilla *et al.* 2000.) Recent preprints by Galanti and Olami (1999) and Gat and Olami (2000) have examined the nature of vibrational states near the mobility edge. Using scalar vibrations, they find numerical evidence that vibrations may belong to a different “universality class” from electrons.

The concerns of the present paper are not so much the formal questions of universality, but instead specific questions of how vibrational eigenstates look in real materials. Experiment does not give access to vibrational eigenvectors or to electron wavefunctions. Much of the information about these states comes from computer studies. Most of these studies use simplified “toy” models, such as “scalar vibrations” where the vector displacement of an atom is replaced by a scalar variable, or hypothetical structures with fractal geometries (Alexander and Orbach, 1982; Nakayama *et al.*, 1994; Kantelhardt *et al.*, 1998). Here we look at properties of vibrational eigenstates near the mobility edge in the most realistic model presently available for amorphous Si. We use vector vibrations and find that the localization length diverges in the usual way as the mobility edge is approached from the localized side. We find no evidence for a diverging correlation length on the delocalized side. These results seem to agree with those of Gat and Olami but not with those of Galanti and Olami. We believe that our results are reliable, accurately portraying how vibrations look in our model, and perhaps generally in glasses, at energies distant by more than 1 meV from the mobility edge. It is likely that for energies distant by less than 1 meV from the mobility edge, correlation lengths diverging with a universal critical exponent occur on both sides of the mobility edge, but this information is outside our grasp.

The usual method for extracting information about the critical regime from finite systems in $d = 3$ is to use finite-size scaling combined with calculations averaged

over large ensembles (Kramer and MacKinnon 1993). By this method one is able indirectly to extract information from states whose localization length is comparable to the sample size, provided that the scaling hypothesis is accepted. Our method is completely different. Our system is large ($L = 44\text{\AA}$) and has more than 400 eigenstates which are well-localized within this system size. We can look directly at these eigenstates to see whether they decay exponentially. Averaging over groups of states in an energy interval of 1 meV enhances the quality of the measured decay constants, but even single states can be examined and measured. For the case of glasses with only a few percent of states localized, the mobility edge is easy to locate (to within 1 meV) without ensemble averaging. This was also found by Sheng, Zhou, and Zhang (1994). The direct procedure is complementary to, and provides a necessary reality check on the usual scaling methods. It does not work well for simpler model systems or systems with very large disorder. For example, Feldman *et al.* (1993) artificially pushed ω_c deeper into the spectrum of amorphous Si by adding random mass disorder. At energies a few meV distant from the mobility edge, eigenstates were not sharply localized within the finite sample, and the clarity of location of ω_c was lost.

We study amorphous silicon in harmonic approximation, using a realistic model which we have already studied extensively. Many of these studies are summarized in a paper hereafter referred to as I (Allen *et al.* 1999). Amorphous Si has approximate tetrahedral coordination, and can be called an “over-constrained network glass.” Even though it is not an especially typical glass, we suspect the vibrational properties under discussion here have much in common with other glasses. Atomic coordinates were generated by Wooten using the algorithm of Wooten, Weiner, and Weaire (1985), with 4096 atoms in a cubic box of side $L = 44\text{\AA}$, continued periodically to infinity. The coordinates were relaxed to a local minimum of the Stillinger-Weber potential (Stillinger and Weber, 1985), which is then used to find the harmonic restoring forces. Eigenvectors and eigenfrequencies were computed on the Linux cluster Galaxy (ref: <http://www.galaxy.ams.sunysb.edu>) using the Scalapack (ref: <http://www.netlib.org/scalapack>) routine PDSYEV. The calculation used 20 Pentium II (400 Mhz) processors and required CPU time of 4.5 hours (including verification of the correctness of the result). The distribution of eigenfrequencies (which are all real) is shown in Fig. 1 of I. Finkemeier and von Niessen (1998) have made a systematic study of this model and several related ones, including more detailed size-dependence than we have done, as well as some variation with disorder. Their results are for vibrational densities of states and localization properties are very similar to ours where they overlap. In addition, they discovered a surprising insensitivity of the location of the mobility edge to the

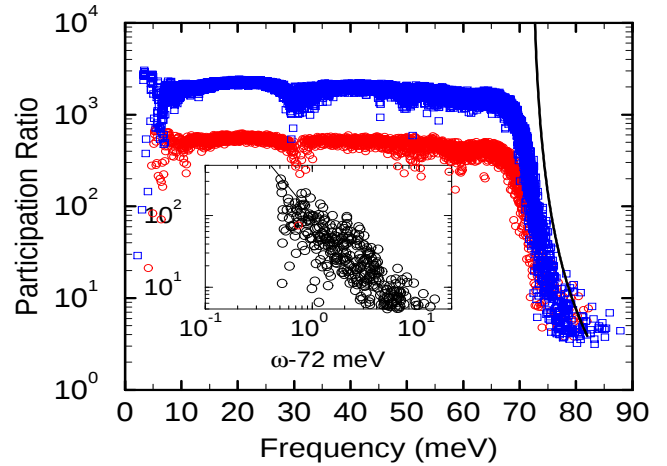


FIG. 1. Participation ratio for normal modes of the 4096-atom model (higher lying data, plotted as squares) and for the 1000-atom model (lower lying data, plotted as circles) plotted versus mode energy. The thick solid line seen at higher energy is the scaling result using the dashed line from Fig. 2 as discussed in the text. The inset shows the higher frequency data for the 4096-atom model on a logarithmic frequency scale, and a straight line whose equation is $p \propto (\omega - 72\text{meV})^{-3p}$ with exponent $p = 0.6$.

degree of amorphous disorder introduced in the model.

The definition of a localized state is exponential decay of the eigenvector with distance from some center $\vec{R}_0$:

$$|\vec{\epsilon}_i(\vec{R}_n)|^2 = |a_i(\vec{R}_n)|^2 \exp(-2|\vec{R}_n - \vec{R}_0|/\xi_i) \quad (1)$$

where $a_i(\vec{R}_n)$ isolates a factor which is not systematic but instead fluctuating in magnitude and sign. These fluctuations are random in the sense that one expects an ensemble of similarly prepared systems to show eigenstates for which the localization length ξ_i has “universal” behavior near the mobility edge, and the deviations $a_i - \bar{a}$ from exponential fall-off to be “pseudo-random” with zero mean ($\bar{a} = 0$) and distribution $P(a)$ independent of $\vec{R}_n$. Representative plots are shown in Fig. 5 of I. In order to confirm numerically that exponential decay is occurring, it is desirable to have $|\vec{\epsilon}_i|^2$ decrease by at least 100 over the maximum available $|\vec{R}_n - \vec{R}_0|$ which is $L/2$ or $22\text{\AA}$. This means that accurately determined values of ξ are $8\text{\AA}$ or less. Very large system sizes are needed to measure the large values of ξ expected close to the mobility edge.

Our previous studies on various size models have shown that most properties are reproducible from model to model. Figure 1 shows how reproducible is the participation ratio p_i defined as (Bell and Dean, 1970)

$$p_i = \frac{[\sum_n |\vec{\epsilon}_i(\vec{R}_n)|^2]^2}{\sum_n |\vec{\epsilon}_i(\vec{R}_n)|^4}. \quad (2)$$

The numerator is simply the normalization factor, equalling 1 for normalized vectors. If the mode i is a

pure plane wave, the denominator sums to $1/N$, so p_i is the number of atoms, N . If the mode i is localized on a single site, the denominator is 1 and $p_i = 1$. Roughly speaking, p_i measures the number of atoms which participate in the vibration. To be more quantitative, the normalization integral can be written as

$$1 = \int d\vec{r} \rho(\vec{r}) |a_i(\vec{r})|^2 e^{-2r/\xi} \quad (3)$$

where the integral goes over the volume V of a 4096-atom cell, and the density $\rho(\vec{r})$ is $\sum_n \delta(\vec{r} - \vec{R}_n)$. Approximating the density as N/V and $|a_i(\vec{r})|^2$ by its average $\overline{a^2}$, for a state decaying well within one cell volume we obtain $\overline{a^2} \approx (L/\xi)^3/\pi N$. Making the same approximations to evaluate the denominator of Eq.(2), we obtain

$$p \approx 8\pi N (\xi/L)^3 \overline{a^2}^2 / \overline{a^4} \approx (8\pi N/3) (\xi/L)^3, \quad (4)$$

where the assumption is made that the random numbers a_i have a Gaussian distribution.

According to scaling theory, eigenvectors for states near the mobility edge (which serves as the critical point) should be characterized by a correlation length. On the localized side of the mobility edge, the decay length serves as the correlation length. The correlation length should diverge upon approaching the mobility edge. In the “critical region” the divergence is characterized by an exponent ν ,

$$\xi \propto |\omega - \omega_c|^{-\nu} \Rightarrow p \propto |\omega - \omega_c|^{-3\nu}. \quad (5)$$

The exponent ν is supposed to be “universal,” that is, the same for all systems with time-reversal symmetry, and is found to have the value $\nu = 1.57 \pm 0.02$ by numerical study of electron models in three dimensions (Ohtsuki *et al*, 1999). The data for p_i are sufficiently dense that we can test this. We choose only modes with $\omega_i > 72.5$ meV, with $p_i < 300$. Making log-log plots of p versus $\omega - \omega_c$ for various choices of ω_c (see the inset to Fig. 1), the data are roughly consistent with power laws, but precision is low and it is not possible even to decide where the mobility edge lies with much accuracy, much less to find a critical exponent. The data fit roughly to $\xi \propto (\omega - 69 \text{ meV})^{-1.5}$, $(\omega - 70 \text{ meV})^{-1.2}$, $(\omega - 71 \text{ meV})^{-0.75}$, and $(\omega - 72 \text{ meV})^{-0.6}$. Therefore we try a different method which uses more of the information in the eigenvectors.

For each mode in the spectrum we have located the atom $\vec{R}_0$ on which $|\vec{\epsilon}_i|^2$ is maximum, and computed the correlation function

$$f_i(R) = \frac{\sum_n |\vec{\epsilon}_i(\vec{R}_n)|^2 \bar{\delta}(R - |\vec{R}_n - \vec{R}_0|)}{\sum_n \bar{\delta}(R - |\vec{R}_n - \vec{R}_0|)} \quad (6)$$

where $\bar{\delta}(x)$ is a rectangularly shaped approximation to a delta function with width $0.2\text{\AA}$. The correlation functions $f_i(R)$ were then averaged over all states i with ω_i

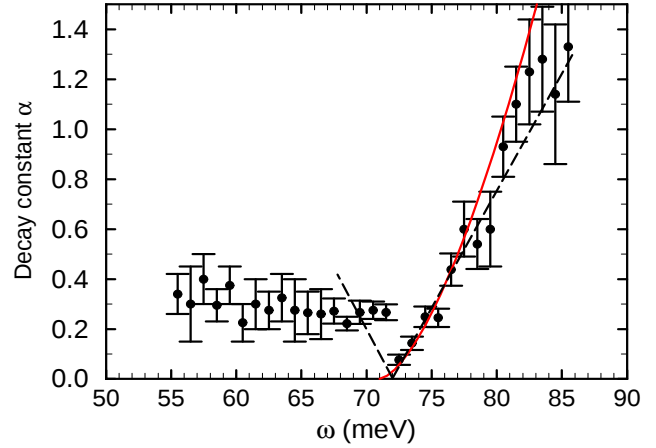


FIG. 2. Decay constant $\alpha = 2/\xi$ in reciprocal Angstroms versus energy ω in meV for vibrations in amorphous silicon. Dashed lines show scaling behavior with exponent $\nu=1$. The curved solid line shows scaling behavior with $\nu=1.57$

in intervals $(\omega, \omega + d\omega)$ of width $d\omega=1$ meV. This means typically 100 states were averaged. These averaged correlation functions $f(\omega, R)$ were then plotted semilogarithmically over the spatial range $0 < R < 20\text{\AA}$. For all $\omega > 72$ meV, the semilog graph fell linearly (with random fluctuations) over a range $R_1 < R < 20\text{\AA}$, and decay constants α and errors $\Delta\alpha$ could be found. The distance R_1 below which non-exponential behavior occurred was about $13\text{\AA}$ for the frequency range 72-73 meV, just above ω_c , and decreased steadily to $4\text{\AA}$ as ω increased. Values of α and errors are shown in Fig. 2.

The data for $\omega > 72$ meV are consistent with a linear relation $2/\xi = 0.094(\text{\AA meV})^{-1}(\omega - 72 \text{ meV})$, that is, with exponent $\nu = 1$. These data are also consistent with the curve $2/\xi = 0.03(\text{\AA meV}^{1.57})^{-1}(\omega - 71 \text{ meV})^{1.57}$, that is, with exponent $\nu = 1.57$. These results can be used in Eq.(4) to model the behavior of p_i for $\omega_i > 72$ meV. The linear fit is shown as the solid line on Fig. 1. A much improved fit to the data in Fig. 1 is obtained by shifting the mobility edge down from 72 meV to 70 meV. The disagreement is surprisingly large. Using the fit with $\nu = 1.57$ provides no improvement. The explanation is probably that p_i is dominated by exponential decay (as assumed in Eq. (4)) only very near ω_c where larger system sizes are needed. This problem is avoided when we directly examine the spatial behavior of the eigenstates. The correlation length for delocalized states gives the length scale over which fluctuations in magnitude of the eigenvector decay back to the average value,

$$|\vec{\epsilon}_i(\vec{R}_n)|^2 = |a_i(\vec{R}_n) \exp(-|\vec{R}_n - \vec{R}_0|/\xi_i) + b_i(\vec{R}_n)|^2 \quad (7)$$

where $a_i(\vec{R}_n)$ and $b_i(\vec{R}_n)$ are both pseudorandom with

zero mean. For a normalized state, $\overline{b_i^2}$ is $1/N$. The same correlation function (Eq.(6)) was computed and averaged for states in the range 55–72 meV. The results agree qualitatively with the form

$$\overline{f(R)} = \overline{a^2} \exp(-2R/\xi) + 1/N \quad (8)$$

which is expected if a_i and b_i are uncorrelated. The decay constants $\alpha = 2/\xi$ are plotted on Fig. 2. The value of ξ seems fixed near $7\text{\AA}$. This result contradicts the expectation of scaling theory that ξ should diverge with the same exponent on both sides of the mobility edge.

We believe that the numerical data of Fig. 2 represent reliable values of exponential decay lengths for our model of amorphous Si. In particular, these data show clearly that the mobility edge coincides with a point of apparent divergence of this length on the localized side, and also clearly show an asymmetry between the localized and delocalized side of ω_c . Unfortunately, there is no way from this study to decide whether the measured lengths are close enough to the critical region to test the applicability of scaling theory to this system. Nevertheless, the surprising asymmetry seems to be a real property, similar to what was seen by Galanti and Olami (1999).

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